YJ Planar Schottky Barrier Diode Die Specification

200V 60A, 230mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB230S200AS-290F

Main Products Characterstics

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

I_F = 60A

≤ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.